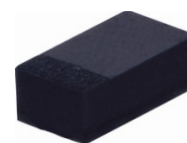


SMD Schottky Barrier Diode

COMCHIP

SMD Diodes Specialist

CDBUR00340(RoHs Device)

 $I_o = 30 \text{ mA}$ $V_R = 40 \text{ Volts}$ 

Features

Designed for mounting on small surface.

Extremely thin package.

Low stored charge.

Majority carrier conduction.

Mechanical data

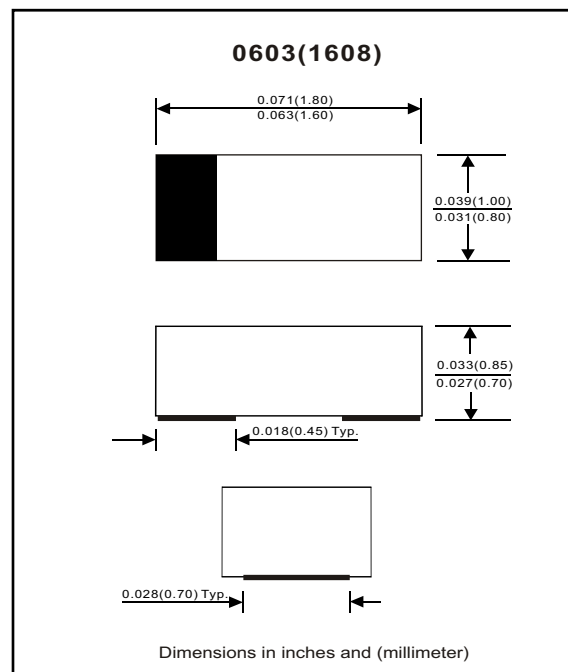
Case: 0603(1608) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).



Maximum Rating (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward current		I_o			30	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}		500		mA
Power Dissipation		P_D			150	mW
Snction temperature		T_{STG}	-40		+125	$^{\circ}\text{C}$
Junction temperature		T_j			+125	$^{\circ}\text{C}$

Electrical Characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 1 \text{ mA DC}$	V_F			0.37	V
Reverse current	$V_R = 30 \text{ V}$ $V_R = 40 \text{ V}$	I_R			0.50 1.00	μA
Capacitance between terimnals	$F = 1 \text{ MHz}$ and 1 VDC reverse voltage	C_T		1.5		pF

REV:A

RATING AND CHARACTERISTIC CURVES (CDBUR00340)

Fig. 1 - Forward characteristics

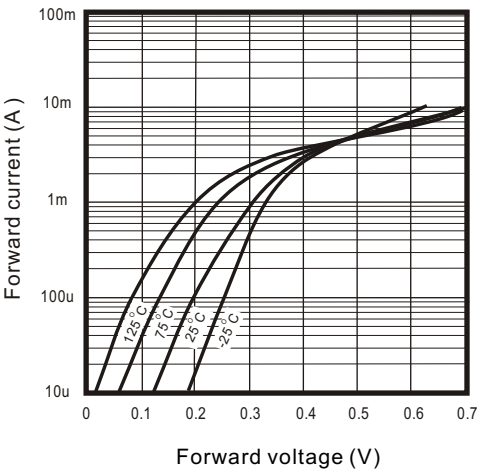


Fig. 2 - Reverse characteristics

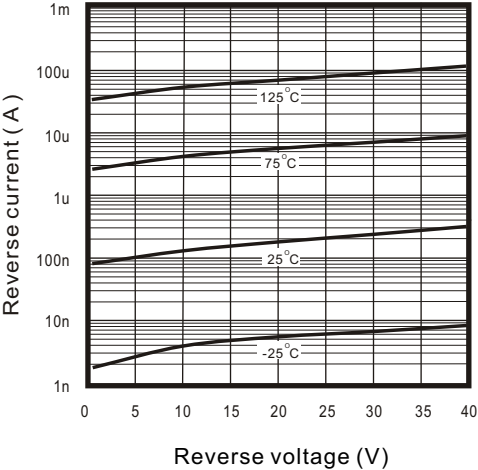


Fig.3 - Capacitance between terminals characteristics

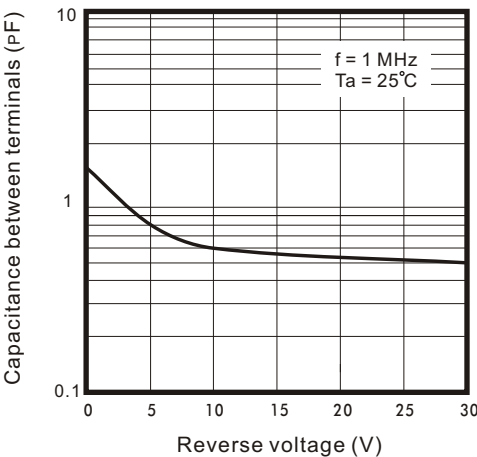


Fig.4 - Current derating curve

